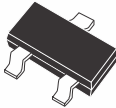


查询CMPD2003-1供应商

CMPD2003
NEW! **CMPD2003C**
NEW! **CMPD2003S**
CMPD2004
NEW! **CMPD2004C**
CMPD2004S

**SURFACE MOUNT
HIGH VOLTAGE SWITCHING DIODE**



SOT-23 CASE

捷多邦, 专业PCB打样工厂, 24小时加急出货

Central
Semiconductor Corp.

DESCRIPTION

The CENTRAL SEMICONDUCTOR CMPD2003, CMPD2003C, CMPD2003S, CMPD2004, CMPD2004C, and CMPD2004S types are silicon switching diodes manufactured by the epitaxial planar process, designed for applications requiring high voltage capability.

The following configurations are available:

CMPD2003	SINGLE
CMPD2003C	DUAL, COMMON CATHODE
CMPD2003S	DUAL, IN SERIES
CMPD2004	SINGLE
CMPD2004C	DUAL, COMMON CATHODE
CMPD2004S	DUAL, IN SERIES

MARKING CODE: A82
MARKING CODE: C3C
MARKING CODE: C3S
MARKING CODE: D53
MARKING CODE: DB7
MARKING CODE: DB6

MAXIMUM RATINGS (T_A=25°C)

	SYMBOL	CMPD2003 CMPD2003C CMPD2003S	CMPD2004 CMPD2004C CMPD2004S	UNITS
Continuous Reverse Voltage	V _R	200	240	V
Peak Repetitive Reverse Voltage	V _{RRM}	250	300	V
Peak Repetitive Reverse Current	I _O	200	200	mA
Continuous Forward Current	I _F	250	225	mA
Peak Repetitive Forward Current	I _{FRM}	625	625	mA
Forward Surge Current, tp=1 ms	I _{FSM}	4000	4000	mA
Forward Surge Current, tp=1 s	I _{FSM}	1000	1000	mA
Power Dissipation	P _D	350		mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150		°C
Thermal Resistance	θ _{JA}	357		°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

	CMPD2003 CMPD2003C CMPD2003S	CMPD2004 CMPD2004C CMPD2004S	UNIT
SYMBOL	MIN	MAX	UNIT
BV _P	250	300	V
I _R		-	nA



SYMBOL	TEST CONDITIONS	CMPD2003		CMPD2004		UNIT
		CMPD2003C	CMPD2003S	CMPD2004C	CMPD2004S	
		MIN	MAX	MIN	MAX	
I_R	$V_R=200V, T_A=150^{\circ}C$		100	-		μA
I_R	$V_R=240V$		-	100		nA
I_R	$V_R=240V, T_A=150^{\circ}C$		-	100		μA
V_F	$I_F=100mA$		1.0	1.0		V
V_F	$I_F=200mA$		1.25	-		V
C_T	$V_R=0, f=1\text{ MHz}$		5.0	5.0		pF
t_{rr}	$I_F=I_R=30mA, \text{Rec. TO } 3.0mA, R_L=100\Omega$		50	50		ns

